

**SEMICONDUCTOR
TECHNICAL DATA**

BC328

EPITAXIAL PLANAR PNP TRANSISTOR

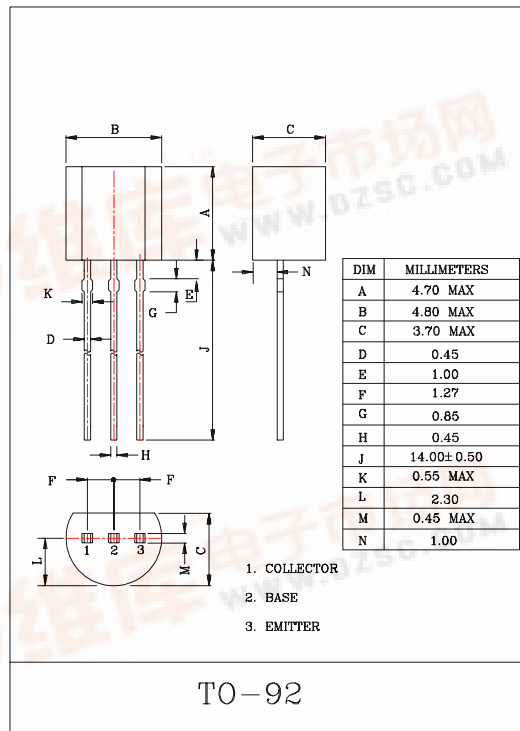
GENERAL PURPOSE APPLICATION,
SWITCHING APPLICATION.

FEATURES

- High Current : $I_C = -800\text{mA}$.
- DC Current Gain : $h_{FE} = 100 \sim 400$ ($V_{CE} = -1\text{V}$, $I_C = -100\text{mA}$).
- For Complementary with NPN type BC338.

MAXIMUM RATINGS ($T_a = 25^\circ\text{C}$)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V_{CBO}	-30	V
Collector-Emitter Voltage	V_{CEO}	-25	V
Emitter-Base Voltage	V_{EBO}	-5	V
Collector Current	I_C	-800	mA
Emitter Current	I_E	800	mA
Collector Power Dissipation	P_C	625	mW
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	-55 ~ 150	$^\circ\text{C}$



ELECTRICAL CHARACTERISTICS ($T_a = 25^\circ\text{C}$)

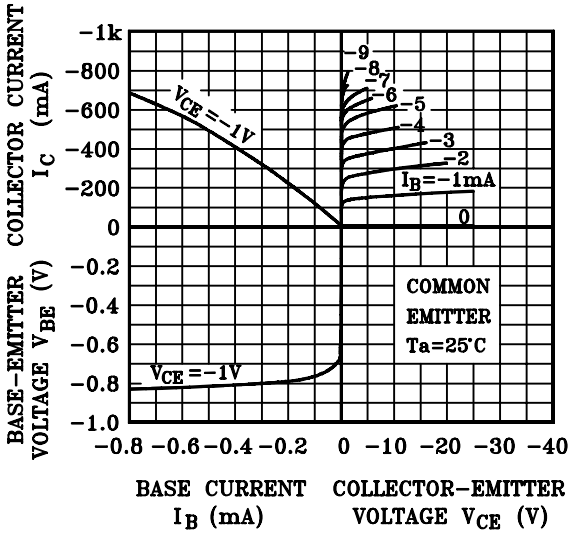
CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	I_{CBO}	$V_{CB} = -25\text{V}$, $I_E = 0$	-	-	-100	nA
DC Current Gain (Note)	h_{FE}	$V_{CE} = -1\text{V}$, $I_C = -100\text{mA}$	100	-	400	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = -500\text{mA}$, $I_B = -50\text{mA}$	-	-	-0.7	V
Base-Emitter Voltage	$V_{BE(ON)}$	$V_{CE} = -1\text{V}$, $I_C = -300\text{mA}$	-	-	-1.2	V
Transition Frequency	f_T	$V_{CE} = -5\text{V}$, $I_C = -10\text{mA}$, $f = 100\text{MHz}$	-	100	-	MHz
Collector Output Capacitance	C_{ob}	$V_{CB} = -10\text{V}$, $f = 1\text{MHz}$	-	16	-	pF

Note : h_{FE} Classification none:100~400 , 16:100~250 , 25:160~400

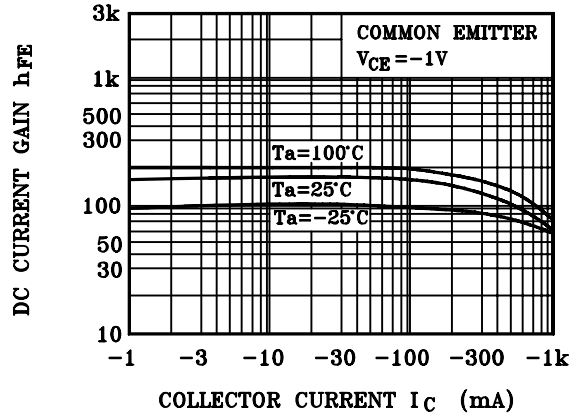


BC328

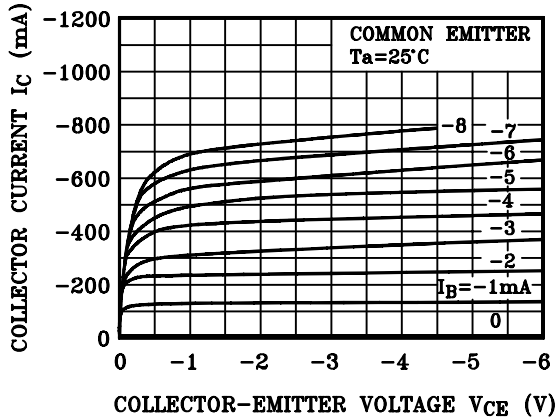
STATIC CHARACTERISTICS



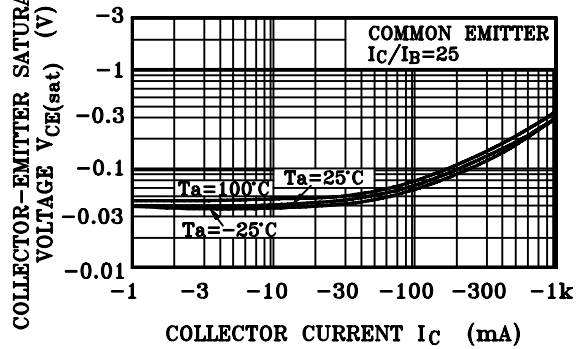
$h_{FE} - I_C$



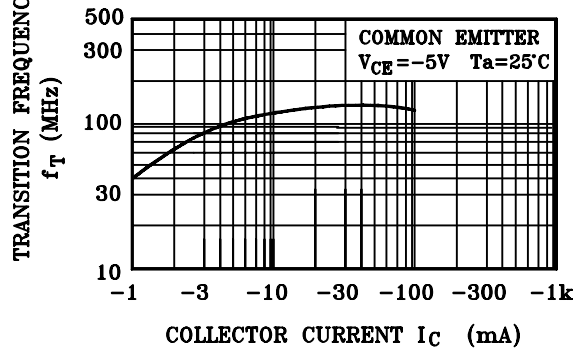
$I_C - V_{CE}$ (LOW VOLTAGE REGION)



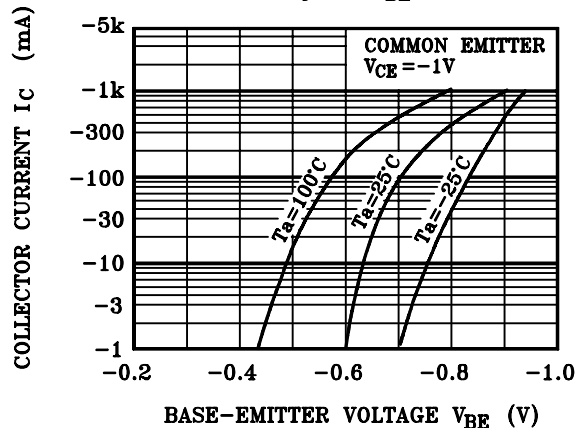
$V_{CE(sat)} - I_C$



$f_T - I_C$



$I_C - V_{BE}$



$P_C - T_a$

